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# ABSTRACT OF THE DISCLOSURE

5 A semiconductor device with a capacitor having a charge retaining capability improved by preventing generation of a leakage current in a capacitor dielectric film, and a manufacturing method of the same are provided. An indium oxide film is formed to continuously cover the upper surfaces of a tungsten film and an interlayer oxide film. A tantalum oxide film is formed to continuously cover the surface of the indium oxide film and a portion of the upper surface of the interlayer oxide film. Another indium oxide film is formed to cover the upper surface of the tantalum oxide film.

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